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Todd R. Abbott **Applicant** Serial No. 09/943,078

August 30, 2001 Filed:

SEMIGONDUCTOR DAMASCENE TRENCH AND METHODS Title THEREOF

MIO 0083 PA Docket No.

Erik J. Kielin Examiner **FAX RECEIVED** Art Unit 2813 7688 Confirm No.:

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Application of

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Applicant

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Sir:

AMENDMENT

This paper is being filed in response to the Office Action dated November 15, 2002 in the identified application, having a reply due date of February 15, 2003. Reconsideration is respectfully requested in light of the amendments and remarks below.

IN THE SPECIFICATION

Please replace the paragraph starting on page 12, line 29 with the following:

Further, where the conductive layer comprises a polysilicon, an optional silicide layer may be desirable. Referring to Fig. 12B, after the formation of the spacers 102 and further doping is performed to define the doped source/drain regions 96, the silicide layer 71 is deposited over the structure 10. For example, after cobalt is deposited and a subsequent anneal process is performed, CoSix is formed on the polysilicon conductive layer 70 and active areas, including the doped source/drain regions 96. The silicide layer 71 serves to lower the resistanc of the polysilicon conductive layer 70. Subsequent